

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (L²-π-MOS V)

2SK4019

Chopper Regulator, DC/DC Converter and Motor Drive Applications

- 4 V gate drive
- Low drain-source ON-resistance : $R_{DS(ON)} = 0.17 \Omega$ (typ.)
- High forward transfer admittance : $|Y_{fs}| = 4.5 S$ (typ.)
- Low leakage current : $I_{DSS} = 100 \mu A$ (max) ($V_{DS} = 100 V$)
- Enhancement mode : $V_{th} = 0.8 \sim 2.0 V$ ($V_{DS} = 10 V, I_D = 1 mA$)

Absolute Maximum Ratings (Ta = 25°C)

| Characteristic | | Symbol | Rating | Unit |
|--|----------------|-----------|----------|------|
| Drain-source voltage | | V_{DSS} | 100 | V |
| Drain-gate voltage ($R_{GS} = 20 k\Omega$) | | V_{DGR} | 100 | V |
| Gate-source voltage | | V_{GSS} | ± 20 | V |
| Drain current | DC (Note 1) | I_D | 5 | A |
| | Pulse (Note 1) | I_{DP} | 20 | A |
| Drain power dissipation ($T_c = 25^\circ C$) | | P_D | 20 | W |
| Single-pulse avalanche energy (Note 2) | | E_{AS} | 180 | mJ |
| Avalanche current | | I_{AR} | 5 | A |
| Repetitive avalanche energy (Note 3) | | E_{AR} | 2 | mJ |
| Channel temperature | | T_{ch} | 150 | °C |
| Storage temperature range | | T_{stg} | -55~150 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Thermal Characteristics

| Characteristic | Symbol | Max | Unit |
|--|----------------|------|--------|
| Thermal resistance, channel to case | $R_{th(ch-c)}$ | 6.25 | °C / W |
| Thermal resistance, channel to ambient | $R_{th(ch-a)}$ | 125 | °C / W |

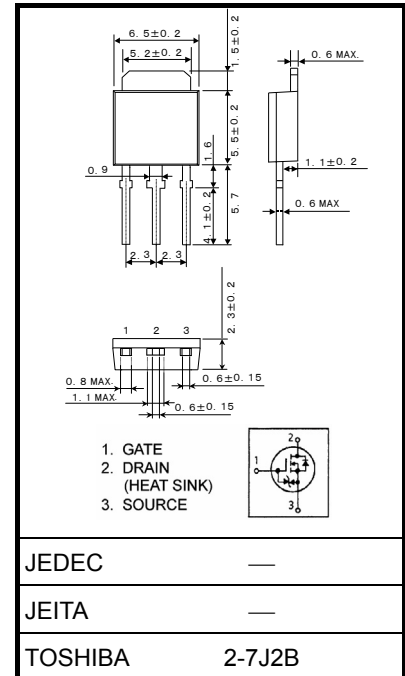
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = 25 V, T_{ch} = 25^\circ C$ (initial), $L = 11.6 mH, R_G = 25 \Omega, I_{AR} = 5 A$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.36 g (typ.)

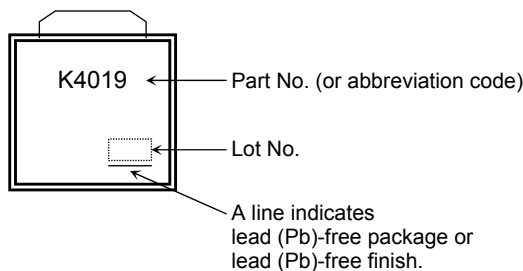
Electrical Characteristics (Ta = 25°C)

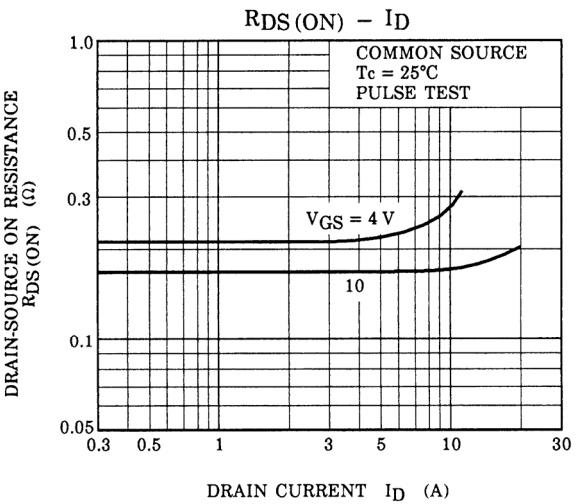
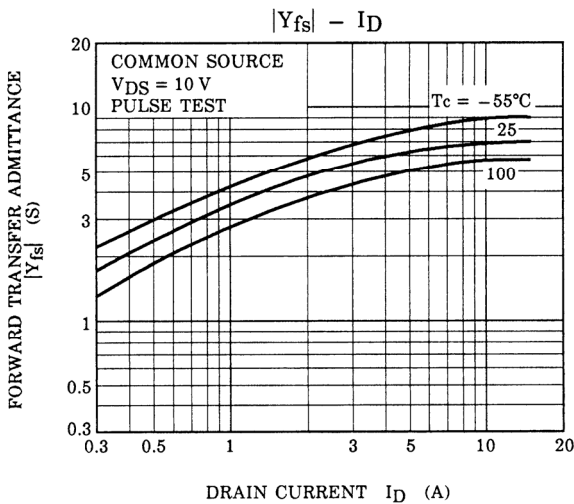
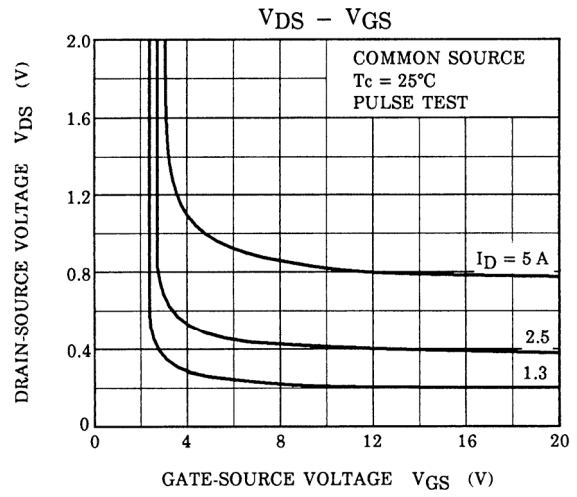
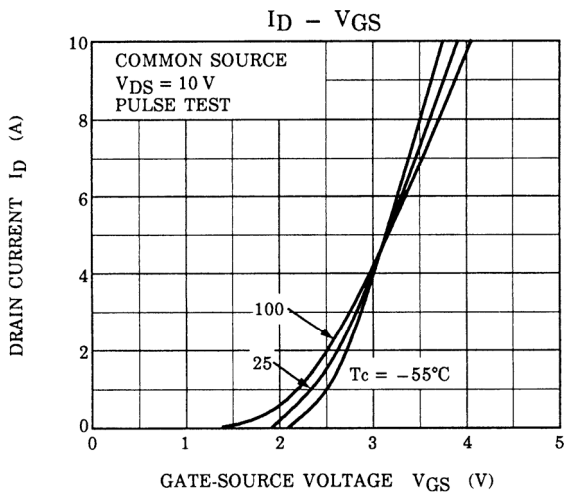
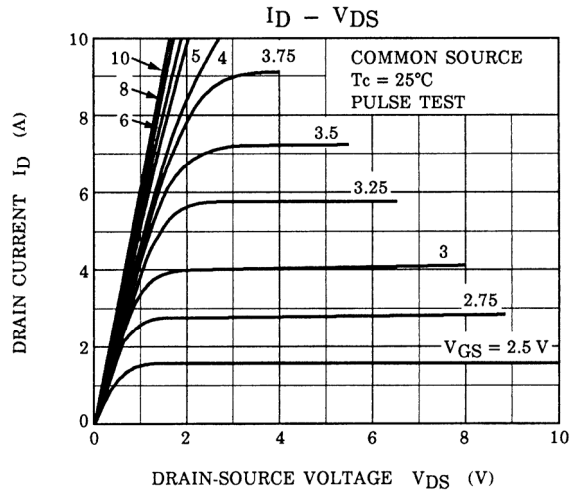
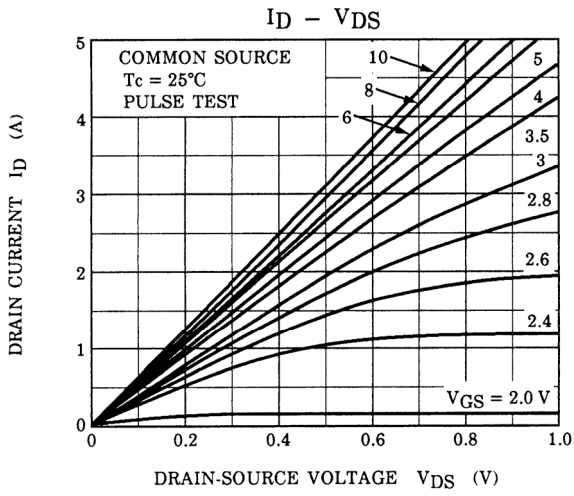
| Characteristic | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---------------|---------------|---|-----|------|----------|---------------|
| Gate leakage current | | I_{GSS} | $V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$ | — | — | ± 10 | μA |
| Drain cutoff current | | I_{DSS} | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$ | — | — | 100 | μA |
| Drain-source breakdown voltage | | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$ | 100 | — | — | V |
| Gate threshold voltage | | V_{th} | $V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$ | 0.8 | — | 2.0 | V |
| Drain-source ON-resistance | | $R_{DS(ON)}$ | $V_{GS} = 4\text{ V}, I_D = 2.5\text{ A}$ | — | 0.22 | 0.30 | Ω |
| | | | $V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$ | — | 0.17 | 0.23 | |
| Forward transfer admittance | | $ Y_{fs} $ | $V_{DS} = 10\text{ V}, I_D = 2.5\text{ A}$ | 2.0 | 4.5 | — | S |
| Input capacitance | | C_{iss} | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | — | 500 | — | pF |
| Reverse transfer capacitance | | C_{rss} | | — | 80 | — | |
| Output capacitance | | C_{oss} | | — | 190 | — | |
| Switching time | Rise time | t_r | <p>$I_D = 2.5\text{ A}$ $V_{GS} = 10\text{ V}$ $V_{DD} \cong 50\text{ V}$ $R_L = 20\ \Omega$ $50\ \Omega$ V_{OUT} $Duty \leq 1\%, t_w = 10\ \mu s$</p> | — | 17 | — | ns |
| | Turn-on time | t_{on} | | — | 25 | — | |
| | Fall time | t_f | | — | 50 | — | |
| | Turn-off time | t_{off} | | — | 195 | — | |
| Total gate charge (Gate-source plus gate-drain) | | Q_g | $V_{DD} \cong 80\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$ | — | 22 | — | nC |
| Gate-source charge | | Q_{gs} | | — | 15 | — | |
| Gate-drain ("Miller") charge | | Q_{gd} | | — | 7 | — | |

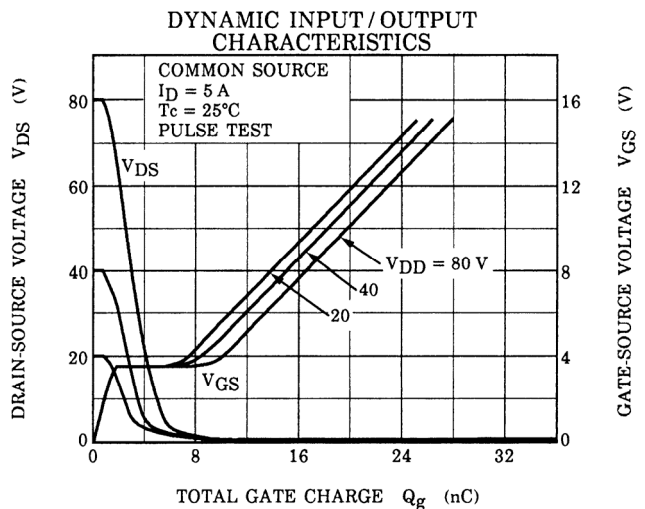
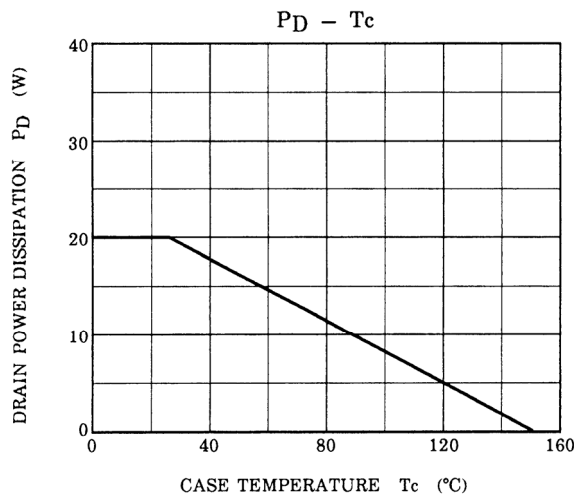
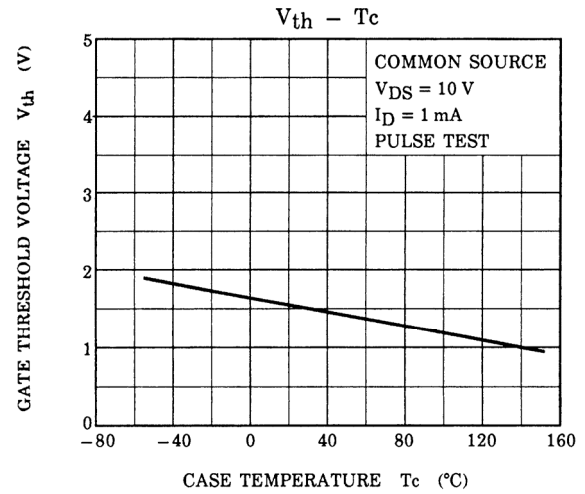
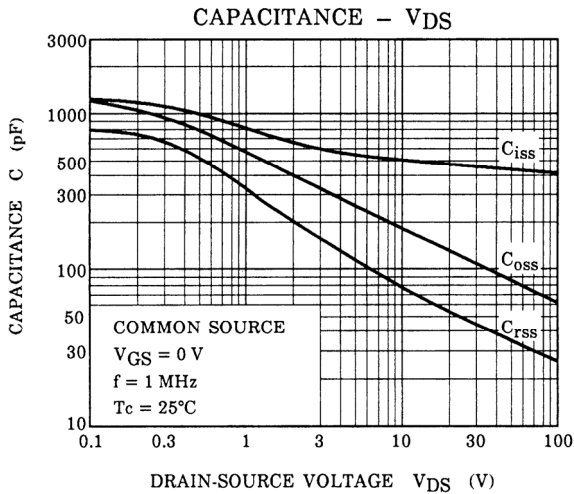
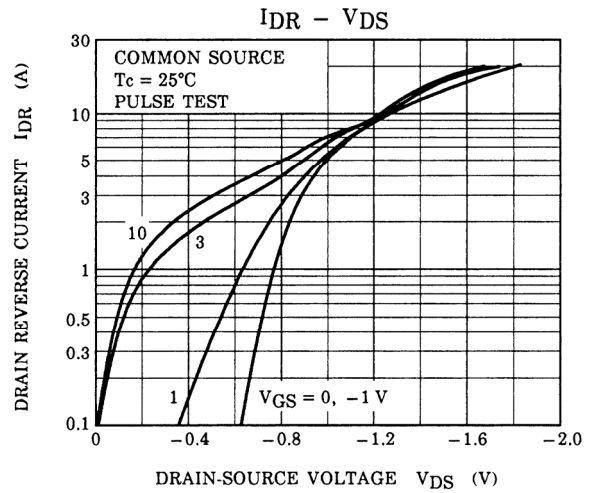
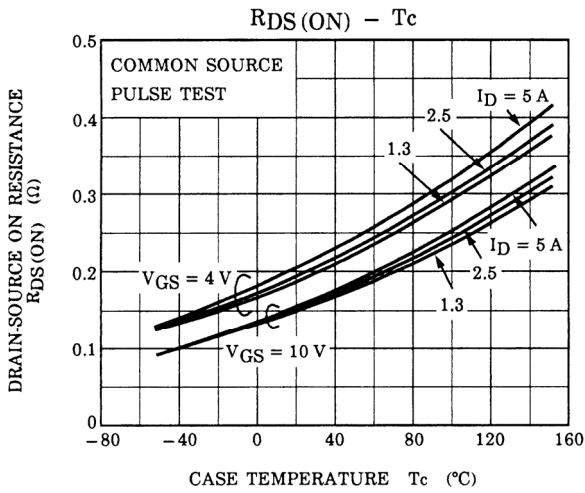
Source-Drain Ratings and Characteristics (Ta = 25°C)

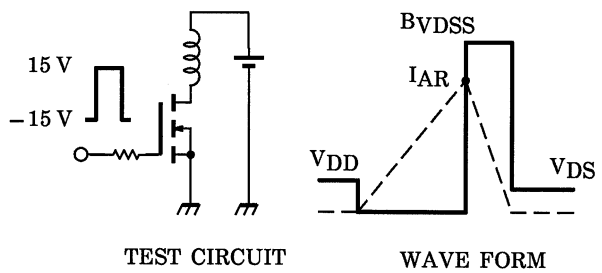
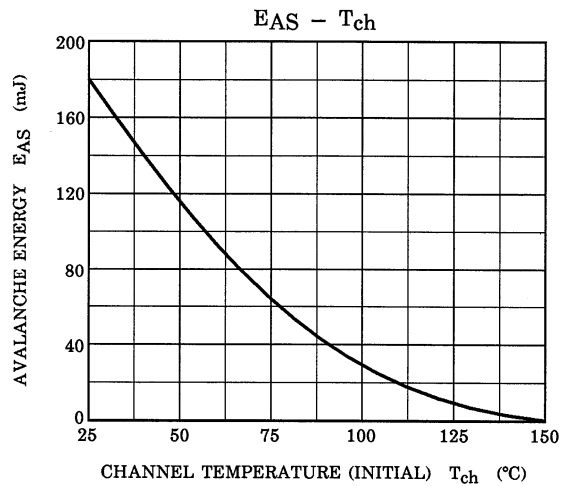
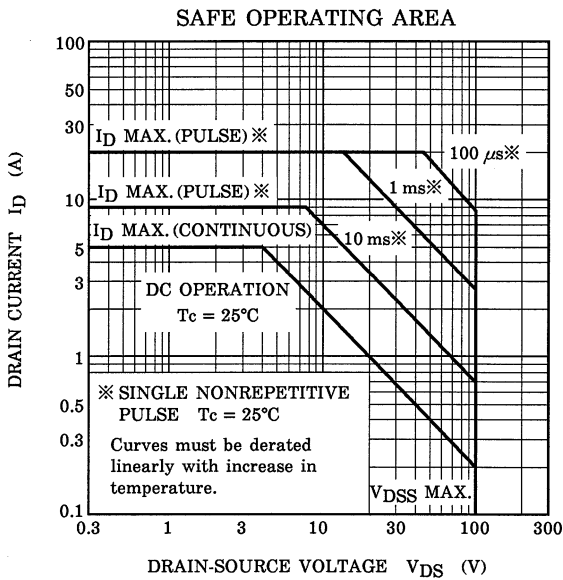
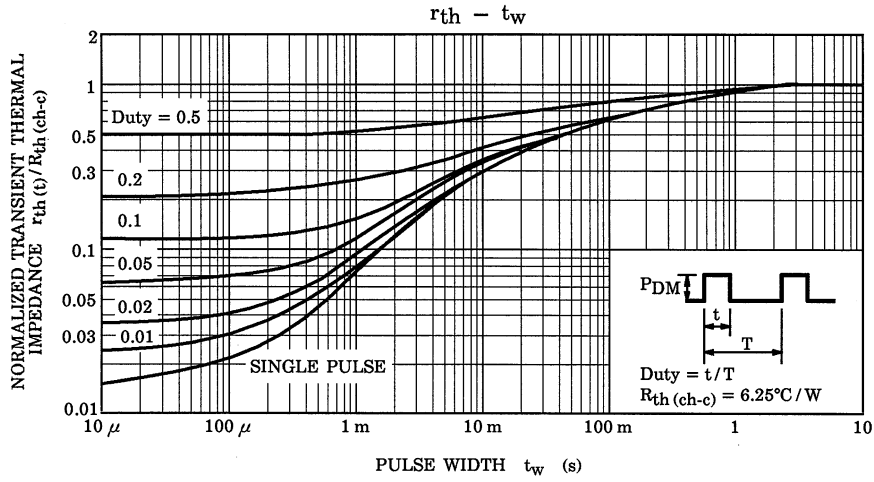
| Characteristic | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|-----------|--|-----|------|------|---------------|
| Continuous drain reverse current (Note 1) | I_{DR} | — | — | — | 5 | A |
| Pulse drain reverse current (Note 1) | I_{DRP} | — | — | — | 20 | A |
| Forward voltage (diode) | V_{DSF} | $I_{DR} = 5\text{ A}, V_{GS} = 0\text{ V}$ | — | — | -1.7 | V |
| Reverse recovery time | t_{rr} | $I_{DR} = 5\text{ A}, V_{GS} = 0\text{ V}, dI_{DR} / dt = 50\text{ A} / \mu s$ | — | 160 | — | ns |
| Reverse recovery charge | Q_{rr} | | — | 0.28 | — | μC |

Marking









$R_G = 25 \Omega$
 $V_{DD} = 25 \text{ V}, L = 11.6 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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